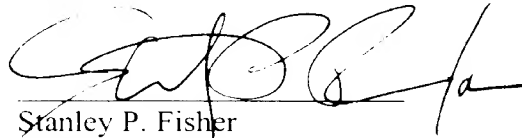


REMARKS

Applicant has amended claim 3 and added claim 40. Applicant has amended the claims in order to remove the multiple dependencies contained therein in accordance with standard U.S. practice, thereby reducing the basic filing fee. No new matter has been added to the application as a result of this amendment.

In view of the above amendments and Applicant's comments stated herein, Applicant respectfully requests an early and favorable action on the merits.

Respectfully submitted,

A handwritten signature in black ink, appearing to read 'Stanley P. Fisher', is written over a horizontal line.

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What is claimed is:

1. A method for manufacturing a semiconductor device, comprising:

5 (1) a step of forming a first film on a major surface of a substrate;

(2) a step of patterning said first film in a predetermined pattern;

(3) a step of placing said substrate having said patterned first film in a process chamber; and

10 (4) a step of placing, on said major surface of said substrate, a pad structure having an opposing major surface to said major surface of said substrate and having a gas ejection section provided on said opposing major surface, and ejecting a predetermined
15 gas from said gas ejection section in a depressurized state in said process chamber while keeping a predetermined distance between said major surface of said substrate and said opposing major surface.

20 2. The method according to claim 1, wherein in said step (4), said pad structure is moved in relative to said substrate.

3. The method according to claim 1 ~~or~~ 2, wherein said substrate is a semiconductor wafer.

25 4. The method according to claim 1, wherein a plurality of gas ejection sections provided on said opposing major surface of said pad structure are placed apart from one another, and said predetermined gas is ejected toward said major surface of said substrate